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Growth Processes and Surface Phase Equilibria in Molecular Beam Epitaxy

With 17 Figures



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Contents

1.	Inti	oduction	1
2.	Bas	ics of MBE Growth	3
	2.1	MBE Apparatus	3
	2.2	Understanding of MBE Growth Processes	5
	2.3	Solid–Vapor Equilibrium for Binary Compounds	8
	2.4	Liquid–Solid–Vapor Equilibrium for Binary Compounds	15
	2.5	Particular III–V Materials	16
		2.5.1 AlAs	16
		2.5.2 InAs	17
		2.5.3 InP	18
		2.5.4 GaP	19
	2.6	Solid–Vapor Equilibrium for Ternary Compounds	20
	2.7	Liquid–Solid–Vapor Equilibrium for Ternary Compounds:	
		Surface Segregation of More Volatile Elements	22
3.	Der	oing and Impurity Segregation Effects in MBE	33
э.	3.1	Point-Defect Equilibria in MBE	ээ 33
	$3.1 \\ 3.2$	Impurity Incorporation in MBE	-36 -36
	J.Z	3.2.1 General Consideration	$-30 \\ -36$
		3.2.2 Manganese Doping of GaAs	$-30 \\ -37$
		3.2.3 GaAs Doping with Zn, Cd, Pb, Mg	39 - 39
		3.2.4 GaAs Doping with S, Se, Te	$\frac{39}{40}$
		3.2.5 GaAs Doping with Amphoteric Impurities: Ge, Si, Sn.	40
	3.3	Impurity Segregation in MBE	41
	$3.3 \\ 3.4$	Interplay Between Impurity Segregation and Diffusion	40
	0.4	in MBE	47
			41
4.	Infl	uence of Strain in the Epitaxial Film	
	on	on Surface-Phase Equilibria	
	4.1	MBE Growth of Lattice-Mismatched Binary Compound	59
	4.2	Growth of Lattice-Matched Solid Solution	
		Formed From Lattice-Mismatched Binaries	66

5.	II–VI Materials	71
6.	Conclusion	75
Inc	lex	83